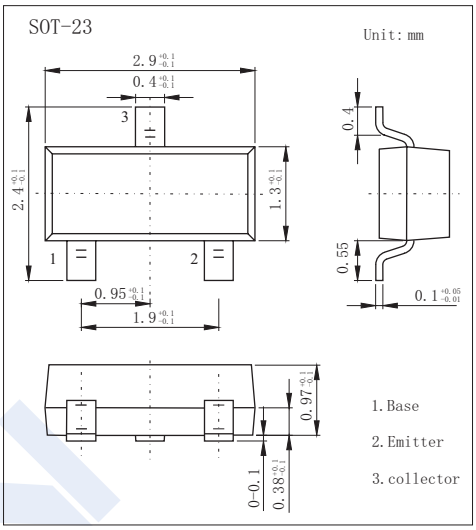
PNP Transistor

BC856C (KC856C)



■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-80	V
Collector - Emitter Voltage	V_{CEO}	-65	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-80			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-65			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -70 V , I_E=0			-100	nA
Collector- emitter cut-off current	I_{CEO}	V_{CE}=- 55 V , I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -100 mA, I_B=- 5mA			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C= -100 mA, I_B= -5mA			-1.1	
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -2mA	420		800	
Collecto output capacitance	C_{ob}	V_{CB}= -10V, f=1MHz			4.5	pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA,f=100MHz	100			MHz

■ Marking

Marking	3C

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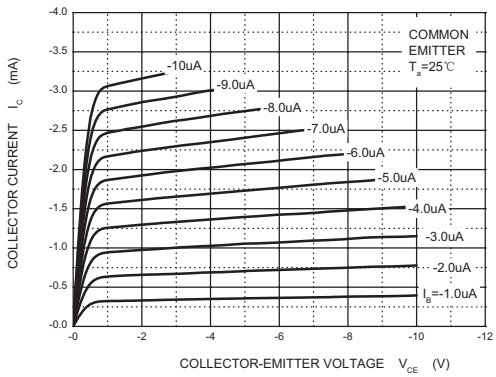
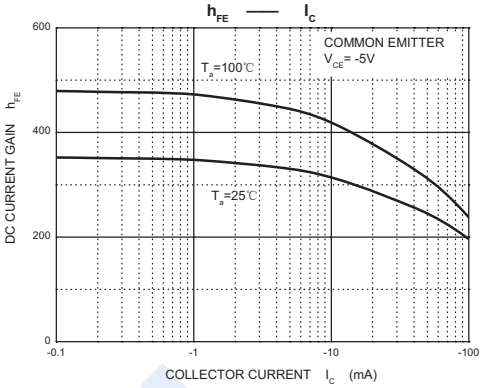
■ Typical Characterisitics

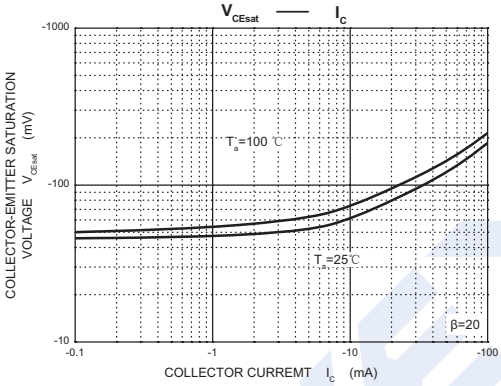
Static Characteristic



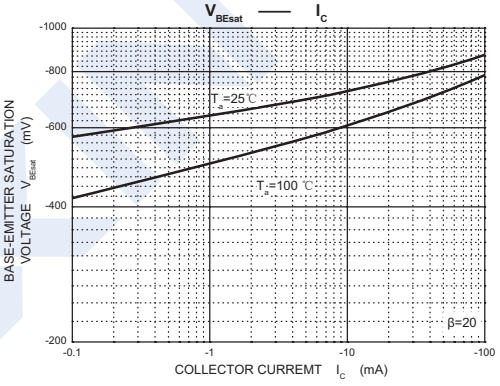
h_{FE} — I_C



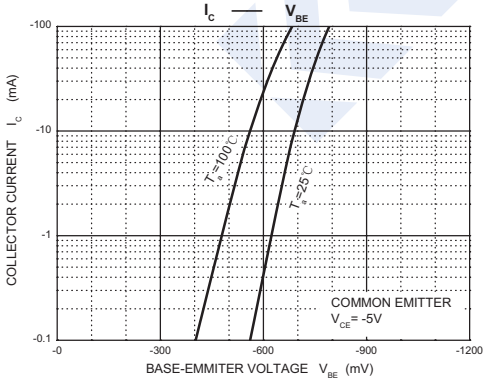
V_{CEsat} — I_C



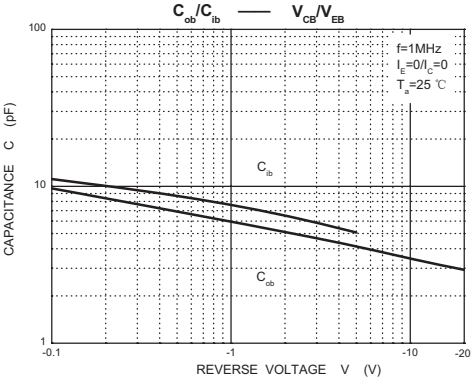
V_{BEsat} — I_C



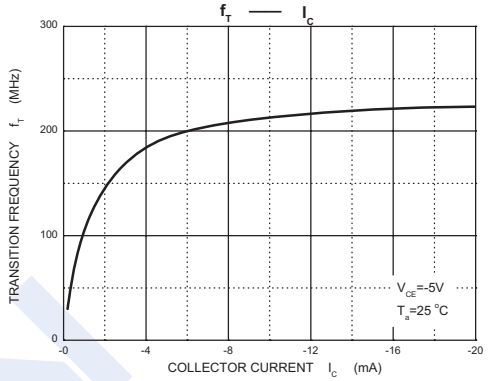
I_C — V_{BE}



C_{ob}/C_{ib} — V_{CB}/V_{EB}



f_T — I_C



P_C — T_a